

MJ11017 PNP SILICON DARLINGTON TRANSISTOR

**SWITCHING REGULATORS PWM INVERTERS
SOLENOID AND RELAY DRIVERS**

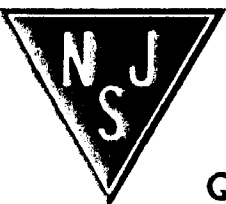
ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

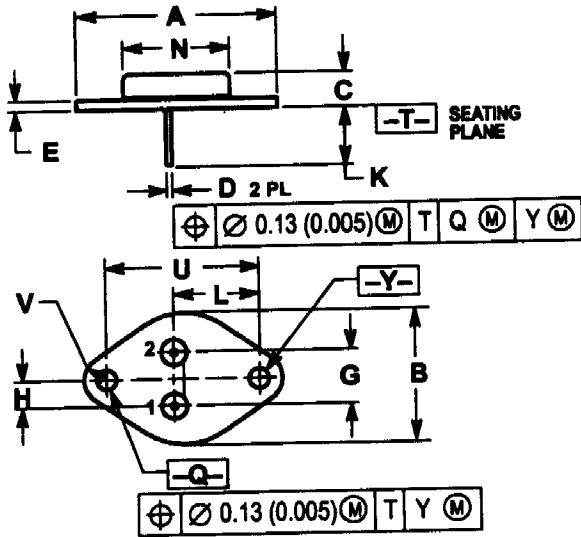
Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	-150	V
Collector-Emitter Voltage	VCEO	-150	V
Collector Current (DC)	IC	-15	A
Collector Dissipation (Tc=25°C)	PC	200	W
Junction Temperature	Tj	200	°C
Storage Temperature	Tstg	-50~150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	ICBO	VCB=-150V, IE=0			10	µA
Collector Cutoff Current	ICEO	VCB=-150V, IB=0			10	µA
DC Current Gain	hFE	VCE=-5V, IC=-10A	1K			
Collector-Emitter Saturation Voltage	VCE(sat)	IC=-6A, IB=-0.6A			-1.5	V

NJ Semi-Constructors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Constructors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Constructors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Constructors encourages customers to verify that datasheets are current before placing orders.





NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
 Y14.5M, 1982.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.560 REF		39.37 REF	
B	—	1.050	—	26.67
C	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.685 BSC		16.89 BSC	
N	—	0.830	—	21.08
Q	0.151	0.185	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

STYLE 1:
 PIN 1. BASE
 2. EMITTER
 CASE: COLLECTOR